APTGF50DH60T1G

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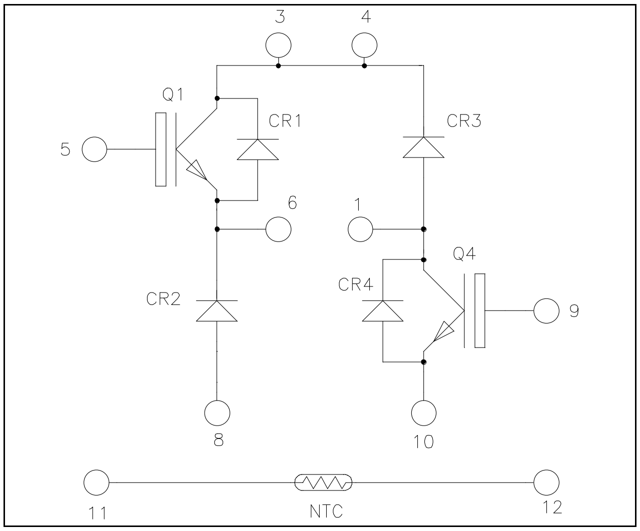
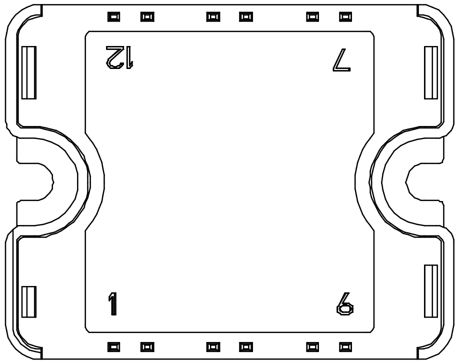
Asymmetrical - Bridge NPT IGBT Power Module

V_{CES} = 600V
I_C = 50A* @ Tc = 80°C





Pins 3/4 must be shorted together

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Non Punch Through (NPT) Fast IGBT
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 100 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Very low stray inductance
  - Symmetrical design
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{CES}	Collector - Emitter Breakdown Voltage		600	V
I_C	Continuous Collector Current	T_C = 25°C	65*	A
		T_C = 80°C	50*	
I_{CM}	Pulsed Collector Current	T_C = 25°C	230	
V_{GE}	Gate – Emitter Voltage		±20	V
P_D	Maximum Power Dissipation	T_C = 25°C	250	W
RBSOA	Reverse Bias Safe Operating Area	T_j = 125°C	100A @ 500V	

* Specification of IGBT device but output current must be limited to 40A to not exceed a delta of temperature greater than 35°C for the connectors.

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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All ratings @ T_j = 25°C unless otherwise specified

Electrical Characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
I_{CES}	Zero Gate Voltage Collector Current	V_{GE} = 0V V_{CE} = 600V	T_j = 25°C			250	µA
			T_j = 125°C			500	
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	V_{GE} =15V I_C = 50A	T_j = 25°C	1.7	2.0	2.45	V
			T_j = 125°C		2.2		
$V_{GE(th)}$	Gate Threshold Voltage	V_{GE} = V_{CE} , I_C = 1mA		4		6	V
I_{GES}	Gate – Emitter Leakage Current	V_{GE} = 20V, V_{CE} = 0V				400	nA

Dynamic Characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
C_{ies}	Input Capacitance	V_{GE} = 0V V_{CE} = 25V f = 1MHz			2200		pF
C_{oes}	Output Capacitance				323		
C_{res}	Reverse Transfer Capacitance				200		
Q_g	Total gate Charge	V_{GE} = 15V V_{Bus} = 300V I_C = 50A			166		nC
Q_{ge}	Gate – Emitter Charge				20		
Q_{gc}	Gate – Collector Charge				100		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) V_{GE} = 15V V_{Bus} = 400V I_C = 50A R_G = 2.7Ω			40		ns
T_r	Rise Time				9		
$T_{d(off)}$	Turn-off Delay Time				120		
T_f	Fall Time				12		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) V_{GE} = 15V V_{Bus} = 400V I_C = 50A R_G = 2.7Ω			42		ns
T_r	Rise Time				10		
$T_{d(off)}$	Turn-off Delay Time				130		
T_f	Fall Time				21		
E_{on}	Turn-on Switching Energy	V_{GE} = 15V V_{Bus} = 400V I_C = 50A R_G = 2.7Ω	T_j = 125°C		0.5		mJ
E_{off}	Turn-off Switching Energy		T_j = 125°C		1		
I_{sc}	Short Circuit data	V_{GE} ≤15V ; V_{Bus} = 360V t_p≤ 10µs ; T_j = 125°C			225		A

Diode ratings and characteristics (CR2 & CR3)

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I_{RM}	Maximum Reverse Leakage Current	V_R=600V	T_j = 25°C			25	µA
			T_j = 125°C			500	
I_F	DC Forward Current		Tc = 80°C		30		A
V_F	Diode Forward Voltage	I_F = 30A			1.8	2.2	V
		I_F = 60A			2.2		
		I_F = 30A	T_j = 125°C		1.5		
t_{rr}	Reverse Recovery Time	I_F = 30A V_R = 400V di/dt =200A/µs	T_j = 25°C		25		ns
			T_j = 125°C		160		
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		35		nC
			T_j = 125°C		480		

CR1 & CR4 are IGBT protection diodes only

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Thermal and package characteristics

Symbol	Characteristic		Min	Typ	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance	IGBT			0.5	°C/W
		Diode			1.2	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz		2500			V
T_J	Operating junction temperature range		-40		150	°C
T_{STG}	Storage Temperature Range		-40		125	
T_C	Operating Case Temperature		-40		100	
Torque	Mounting torque	To heatsink M4	2.5		4.7	N.m
Wt	Package Weight				80	g

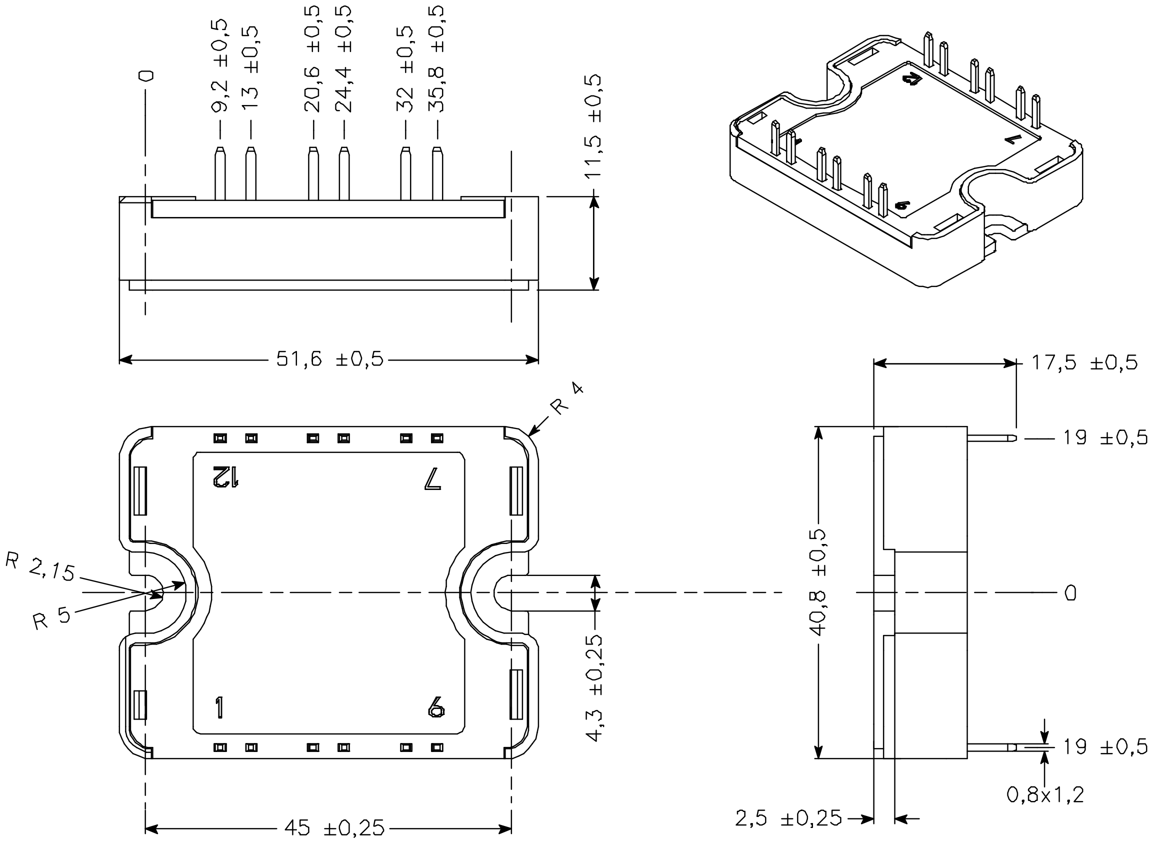
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic		Min	Typ	Max	Unit
R_{25}	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
$B_{25/85}$	$T_{25} = 298.15$ K			3952		K
$\Delta B/B$		T_C=100°C		4		%

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature
R_T: Thermistor value at T

SP1 Package outline (dimensions in mm)



See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

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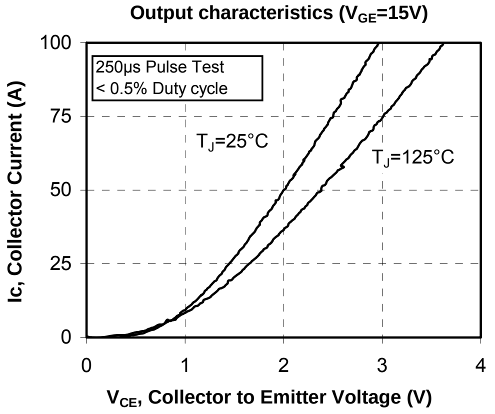
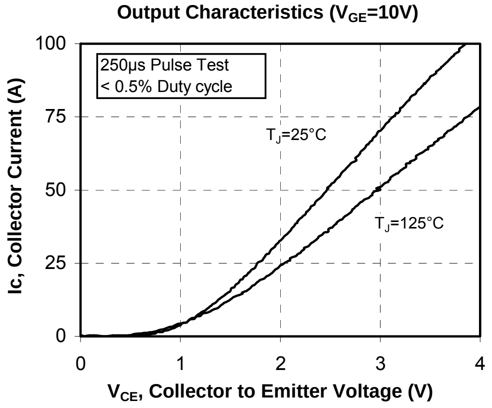
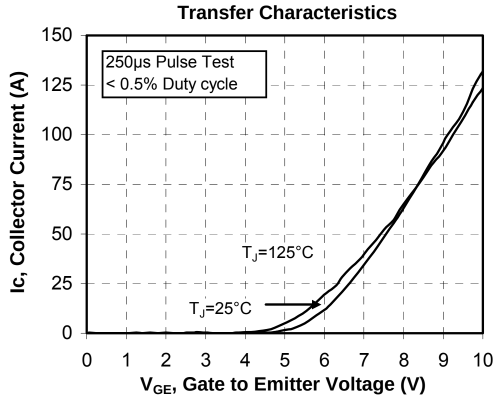
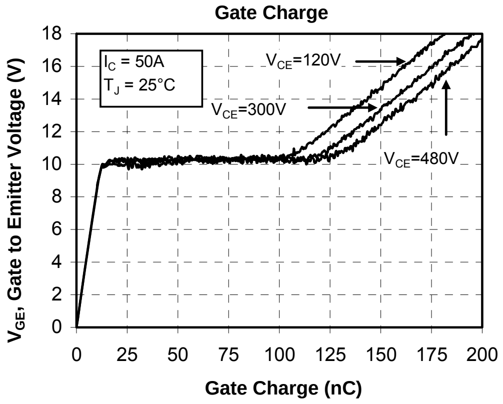
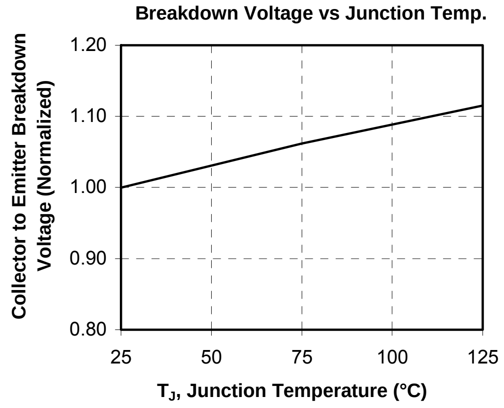
Typical IGBT Performance Curve

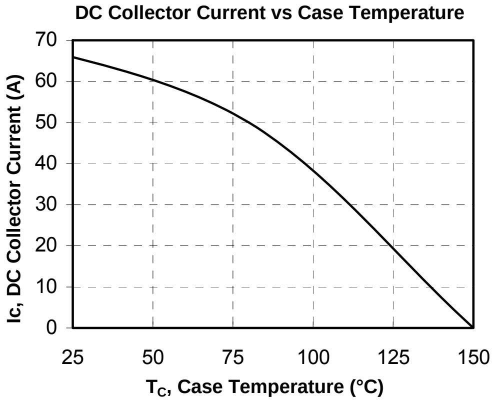

Output characteristics (V_{GE}=15V)


Output Characteristics (V_{GE}=10V)


Transfer Characteristics


Gate Charge


Breakdown Voltage vs Junction Temp.


DC Collector Current vs Case Temperature

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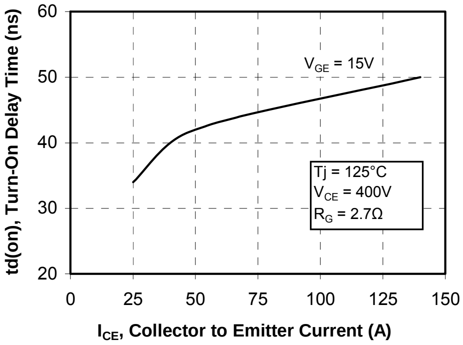
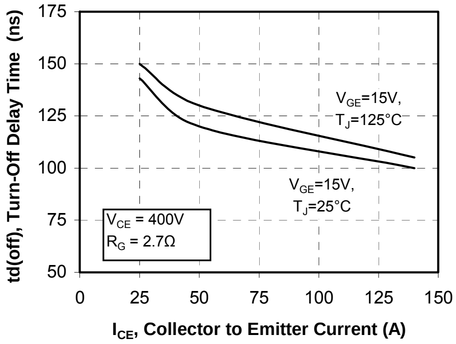
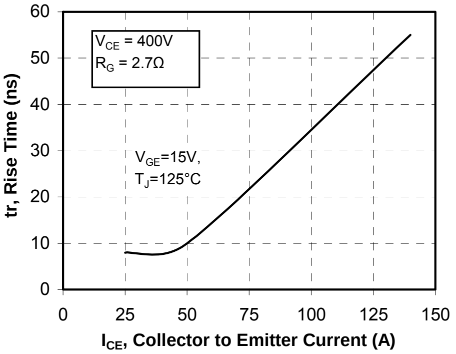
Turn-On Delay Time vs Collector Current



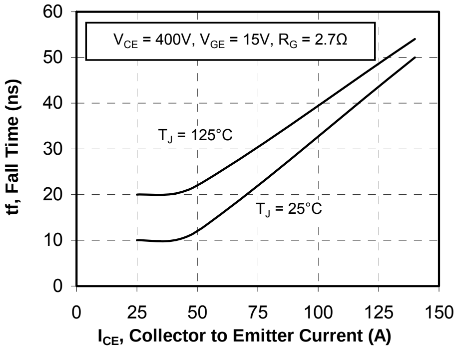
Turn-Off Delay Time vs Collector Current



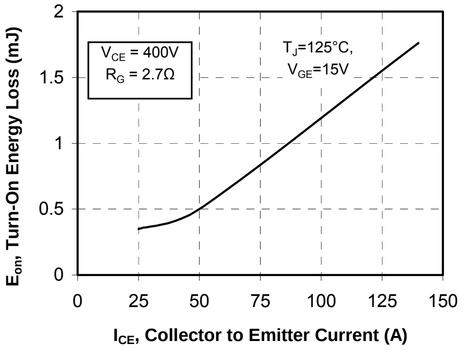
Current Rise Time vs Collector Current



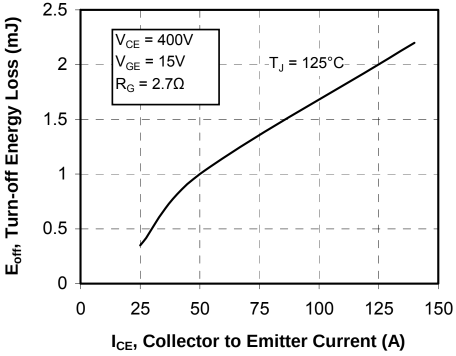
Current Fall Time vs Collector Current



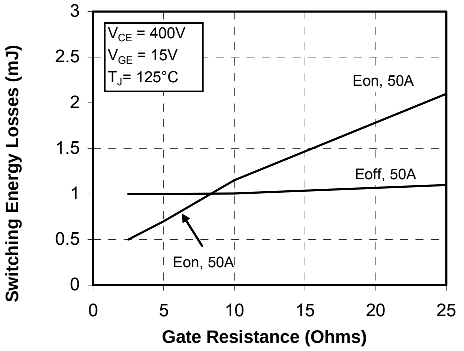
Turn-On Energy Loss vs Collector Current



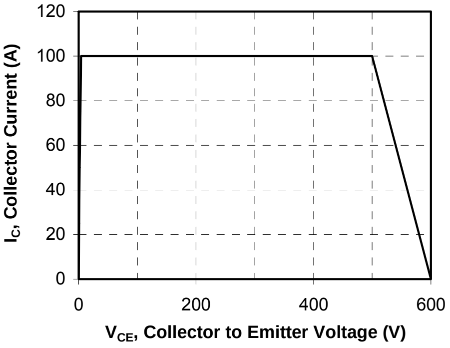
Turn-Off Energy Loss vs Collector Current



Switching Energy Losses vs Gate Resistance



Reverse Bias Safe Operating Area



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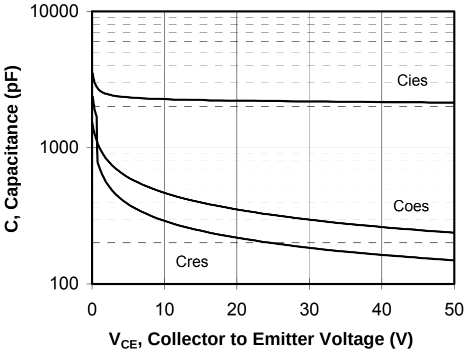
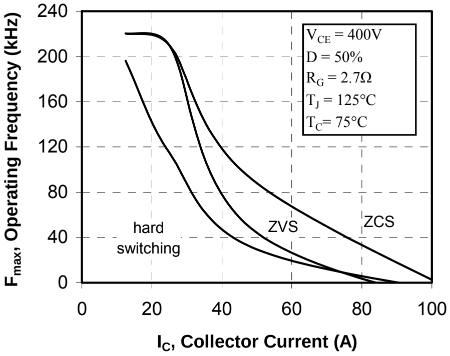
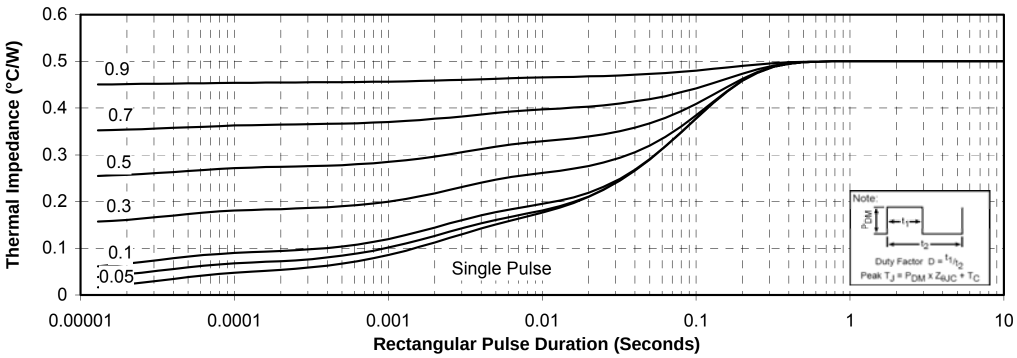
Capacitance vs Collector to Emitter Voltage



Operating Frequency vs Collector Current



Maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration



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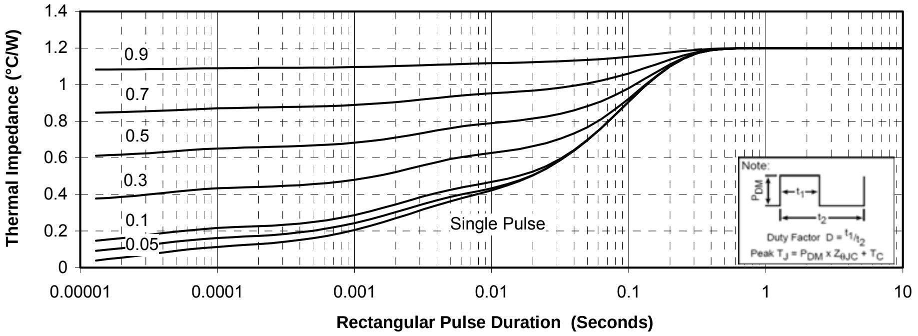
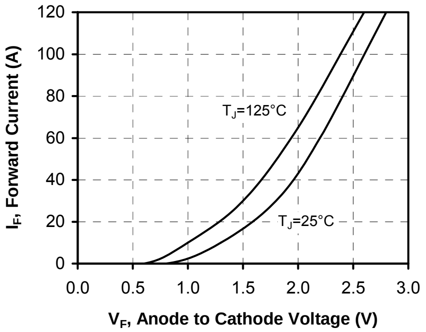
Typical diode Performance Curve

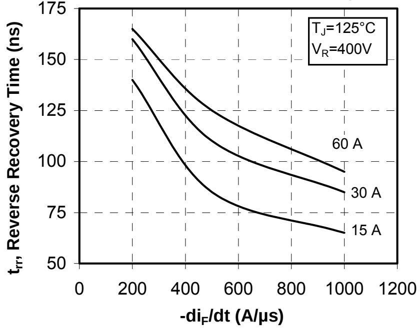
Maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration



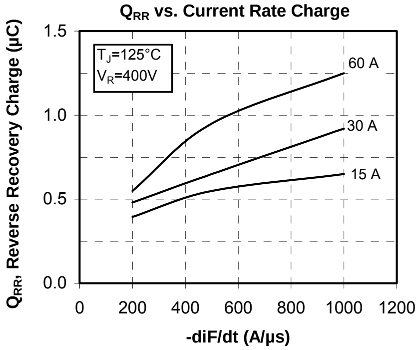
Forward Current vs Forward Voltage



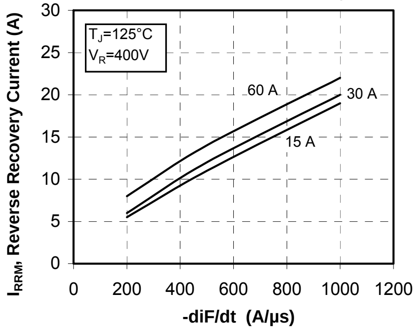
Trr vs. Current Rate of Charge



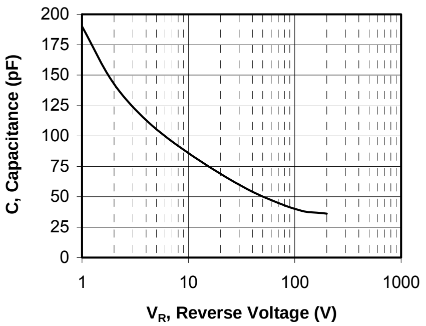
Q_{RR} vs. Current Rate Charge



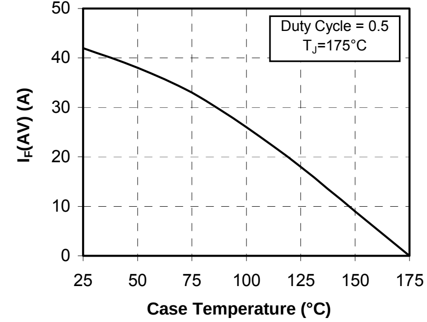
I_{RRM} vs. Current Rate of Charge



Capacitance vs. Reverse Voltage



Max. Average Forward Current vs. Case Temp.



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